

Abstract

Method For Producing Semiconductor Wafers From Monocrystalline Silicon

- 5 The invention provides a process for producing semiconductor wafers from monocrystalline silicon, comprising the pulling of a cylindrical section and subsequently of an end cone of a single crystal of silicon from a melt present in a crucible;
- wherein the pulling speed in the pulling of the end cone remains essentially constant
- 10 compared to the pulling speed in the pulling of the cylindrical section end region; the rotating of the crucible with a speed of rotation and in a direction of rotation during the pulling of the cylindrical section and the end cone of the single crystal; and the dividing of the semiconductor wafers of monocrystalline silicon from the cylindrical section of the single crystal, wherein the pulling speed during the pulling of the end
- 15 cone is at least greater than 0.46 mm/min, while the direction of rotation of the crucible is constantly changed and an amplitude of the speed of rotation before and after the change in direction of rotation is not less than 6 rpm.

[No Available Figure]